GP1S094HCZ0F

Gap : 3mm, Slit : 0.3mm Phototransistor Output, Compact Transmissive Photointerrupter

■ Description

GP1S094HCZ0F is a compact-package, photo-transistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides non-contact sensing. The compact package series is a result of unique technology combing transfer and injection molding.

This device has a wide gap and positioning pins.

■ Agency approvals/Compliance

1. Compliant with RoHS directive

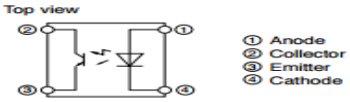
■ Applications

1. Detection of object presence or motion.
2. Example: printer, lens control for camera

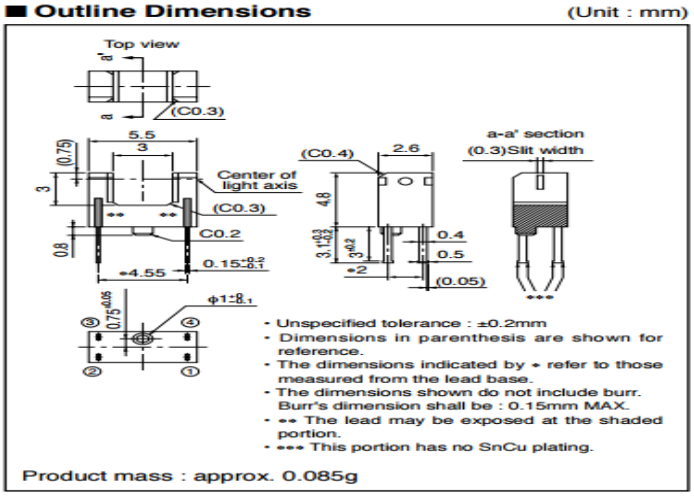
■ Features

1. Transmissive with phototransistor output
2. Highlights:
   - Compact Size
   - Positioning Pin to prevent misalignment
3. Key Parameters:
   - Gap Width : 3mm
   - Slit Width (detector side): 0.3mm
   - Package : 5.5×2.6×4.8mm
4. Lead free and RoHS directive compliant

■ Internal Connection Diagram



■ Outline Dimensions (Unit : mm)



Product mass : approx. 0.085g

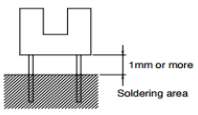
Plating material : SnCu (Cu : TYP. 2%)

Country of origin
Japan

■ Absolute Maximum Ratings (T_a=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	Reverse voltage	V_R	6	V
	Power dissipation	P	75	mW
Output	Collector-emitter voltage	V_{CEO}	35	V
	Emitter-collector voltage	V_{ECO}	6	V
	Collector current	I_C	20	mA
	Collector power dissipation	P_C	75	mW
Total power dissipation		P_{tot}	100	mW
Operating temperature		T_{opr}	−25 to +85	°C
Storage temperature		T_{stg}	−40 to +100	°C
*1Soldering temperature		T_{sol}	260	°C

*1 For 5s or less



■ Electro-optical Characteristics (T_a=25°C)

Parameter			Symbol	Condition	MIN.	TYP.	MAX.	Unit
Input	Forward voltage		V_F	I_F=20mA	–	1.2	1.4	V
	Reverse current		I_R	V_R=3V	–	–	10	μA
Output	Collector dark current		I_{CEO}	V_{CE}=20V	–	–	100	nA
Transfer characteristics	Collector current		I_C	V_{CE}=5V, I_F=5mA	40	–	400	μA
	Collector-emitter saturation voltage		$V_{CE(sat)}$	I_F=10mA, I_C=40μA	–	–	0.4	V
	Response time	Rise time	t_r	V_{CE}=5V, I_C=100μA, R_L=1kΩ	–	50	150	μs
		Fall time	t_f		–	50	150	μs

Fig.1 Forward Current vs. Ambient Temperature

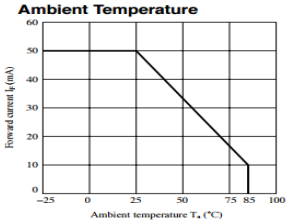


Fig.2 Power Dissipation vs. Ambient Temperature

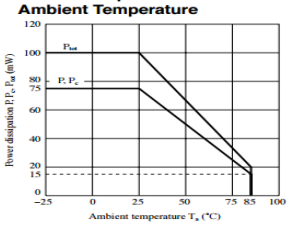


Fig.3 Forward Current vs. Forward Voltage

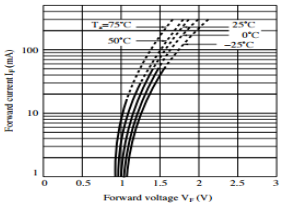


Fig.4 Collector Current vs. Forward Current

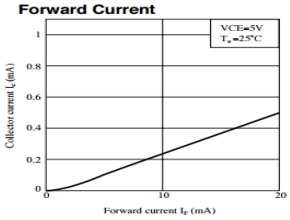


Fig.5 Collector Current vs. Collector-emitter Voltage

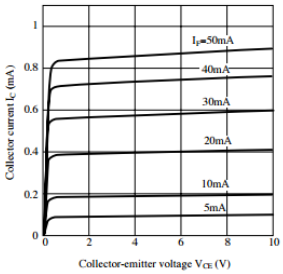


Fig.6 Relative Collector Current vs. Ambient Temperature

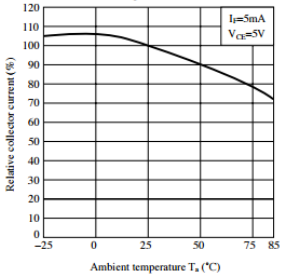


Fig.7 Collector-emitter Saturation Voltage vs. Ambient Temperature

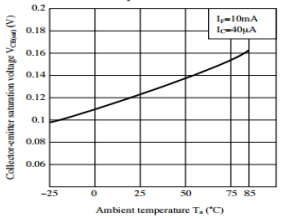


Fig.8 Collector Dark Current vs. Ambient Temperature

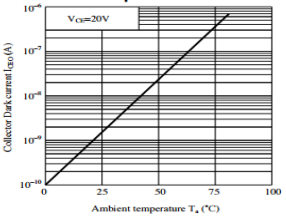


Fig.9 Response Time vs. Load Resistance

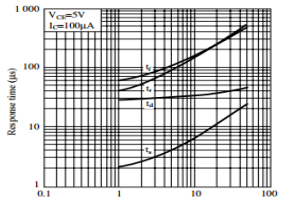
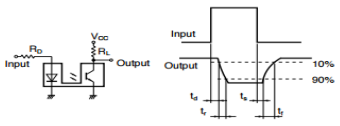


Fig.10 Test Circuit for Response Time



● Design guide

1) Prevention of detection error
To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board
Opaque board shall be installed at place 1.6mm or more from the top of elements.

(Example)

This product is not designed against irradiation and incorporates non-coherent IRED.

● Degradation

In general, the emission of the IRED used in photointerrupter will degrade over time.
In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

● Parts

This product is assembled using the below parts.

• Photodetector (qty. : 1)

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (μs)
Phototransistor	Silicon (Si)	930	700 to 1 200	20

• Photo emitter (qty. : 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3